

isc Silicon NPN RF Transistor

2SC3356

DESCRIPTION

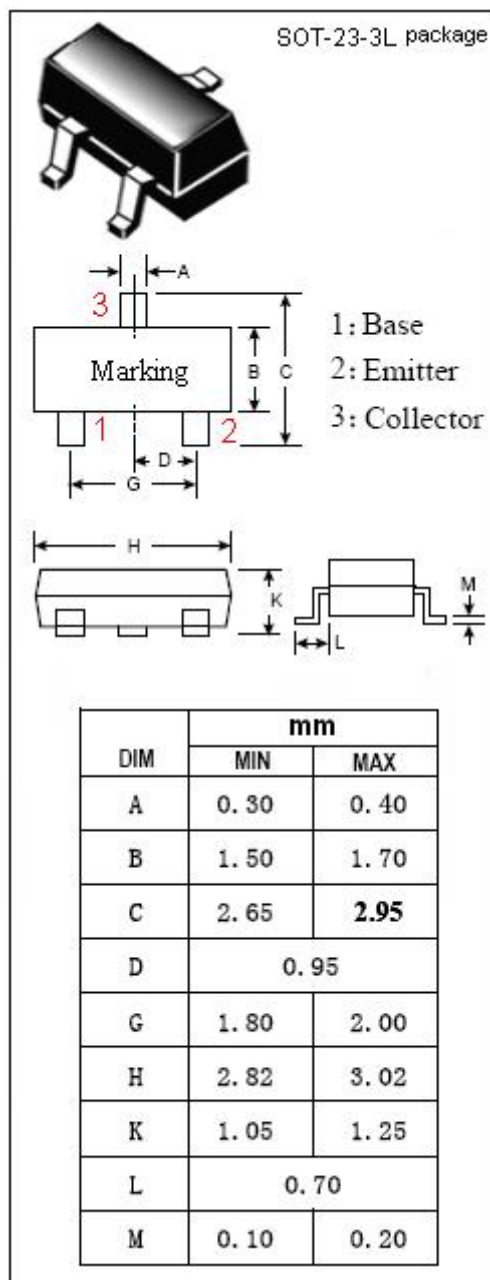
- Low Noise and High Gain
 $NF = 1.1 \text{ dB TYP.}, G_a = 11 \text{ dB TYP.}$
 $@V_{CE} = 10 \text{ V}, I_C = 7 \text{ mA}, f = 1.0 \text{ GHz}$
- High Power Gain
 $MAG = 13 \text{ dB TYP.}$
 $@V_{CE} = 10 \text{ V}, I_C = 20 \text{ mA}, f = 1.0 \text{ GHz}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low noise amplifier at VHF, UHF and CATV band.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	12	V
V_{EBO}	Emitter-Base Voltage	3.0	V
I_C	Collector Current-Continuous	0.1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	0.2	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



isc Silicon NPN RF Transistor**2SC3356****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	$V_{CB}=10\text{V}; I_E=0$			1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=1\text{V}; I_C=0$			1.0	μA
h_{FE}	DC Current Gain	$I_C=20\text{mA}; V_{CE}=10\text{V}$	50		300	
f_T	Current-Gain—Bandwidth Product	$I_C=20\text{mA}; V_{CE}=10\text{V}$		7		GHz
C_{re}	Feed-Back Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$		0.55	1.0	pF
$ S_{21e} ^2$	Insertion Power Gain	$I_C=20\text{mA}; V_{CE}=10\text{V}; f=1.0\text{GHz}$		11.5		dB
NF	Noise Figure	$I_C=7\text{mA}; V_{CE}=10\text{V}; f=1.0\text{GHz}$		1.1	2.0	dB

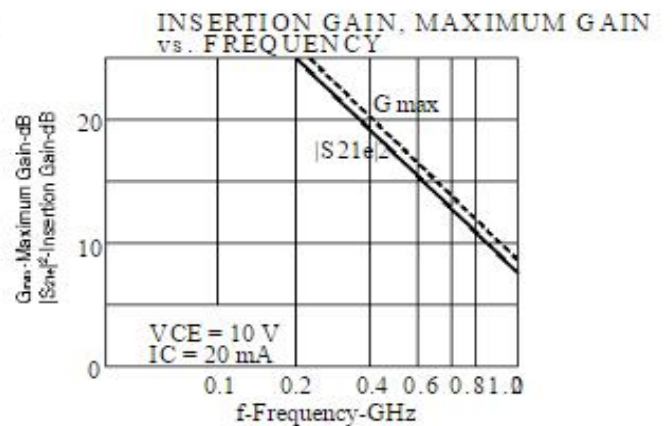
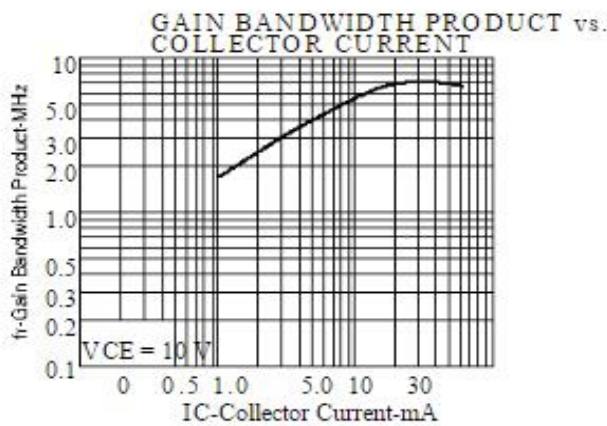
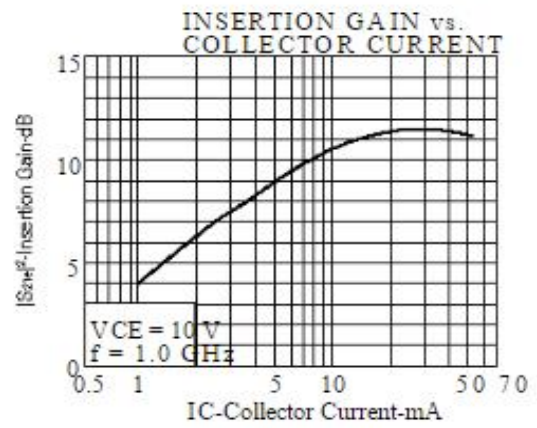
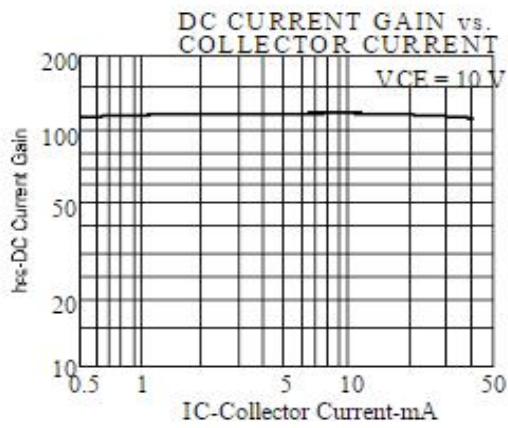
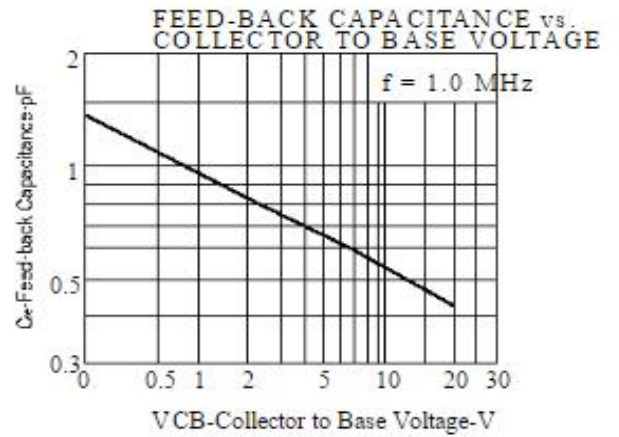
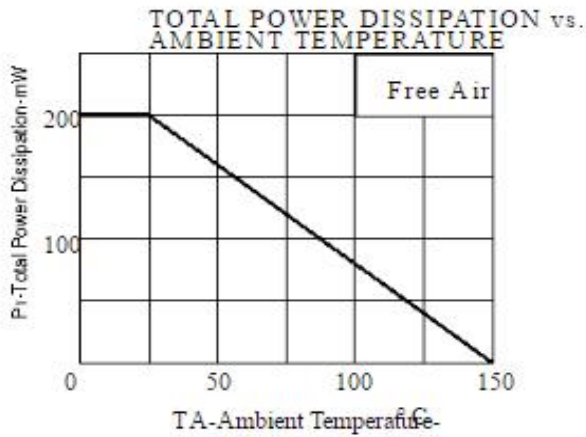
◆ **h_{FE} Classification**

Class	Q	R	S
Marking	R23	R24	R25
h_{FE}	50-100	80-160	125-250

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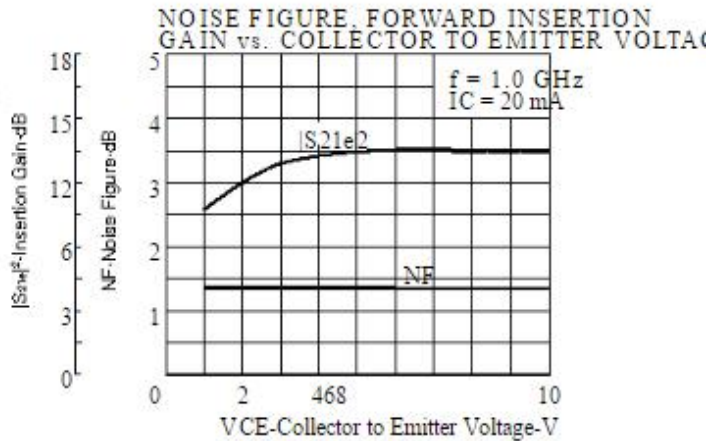
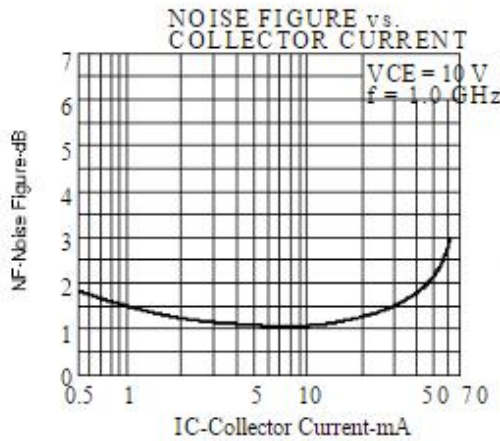
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TYPICAL CHARACTERISTICS (TA = 25°C)



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S-PARAMETER

VCE = 10 V, IC = 5 mA, ZO = 60

f (MHz)	rS11 □ S11	rS21 □ S21	rS12 □ S12	rS22 □ S22
200	0.651 ∟69.3	10.616 129.3	0.051 59.2	0.735 ∟28.1
400	0.467 ∟113.3	6.856 104.4	0.071 54.4	0.550 ∟34.1
600	0.391 ∟139.3	4.852 90.9	0.086 56.0	0.468 ∟33.9
800	0.360 ∟159.2	3.802 81.2	0.101 59.1	0.426 ∟33.6
1000	0.360 ∟176.9	3.098 72.9	0.118 61.0	0.397 ∟35.7
1200	0.361 172.7	2.646 67.3	0.137 63.5	0.373 ∟38.3
1400	0.381 160.3	2.298 59.3	0.157 63.3	0.360 ∟43.0
1600	0.398 152.2	2.071 55.2	0.180 64.1	0.337 ∟45.9
1800	0.423 143.3	1.836 49.0	0.203 63.7	0.320 ∟52.3
2000	0.445 137.6	1.689 46.2	0.220 64.7	0.302 ∟52.2

VCE = 10 V, IC = 5 mA, ZO = 60

f (MHz)	rS11 □ S11	rS21 □ S21	rS12 □ S12	rS22 □ S22
200	0.339 ∟107.0	16.516 108.7	0.035 66.1	0.459 ∟36.6
400	0.258 ∟147.3	8.928 92.1	0.060 71.0	0.343 ∟32.9
600	0.243 ∟167.7	6.022 83.0	0.085 71.9	0.305 ∟29.9
800	0.242 177.0	4.633 76.2	0.109 72.2	0.284 ∟29.4
1000	0.260 164.5	3.744 69.9	0.136 70.4	0.266 ∟31.7
1200	0.269 157.6	3.193 65.7	0.160 69.9	0.246 ∟35.0
1400	0.294 148.7	2.750 58.8	0.187 66.7	0.233 ∟40.4
1600	0.314 143.1	2.479 55.5	0.212 65.2	0.208 ∟43.6
1800	0.343 136.5	2.185 50.1	0.238 62.4	0.190 ∟50.5
2000	0.367 131.4	2.016 47.8	0.254 61.6	0.173 ∟48.3

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